



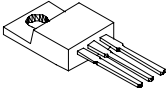
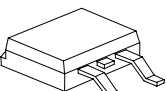
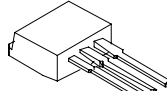
30CTQ.../30CTQ...S /30CTQ...-1
SCHOTTKY RECTIFIER

Applications:

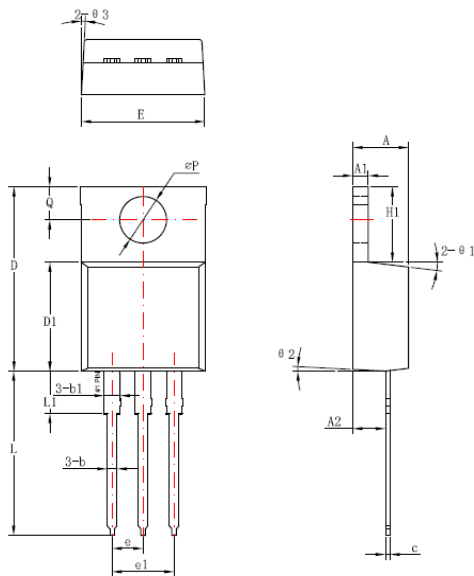
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 175°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

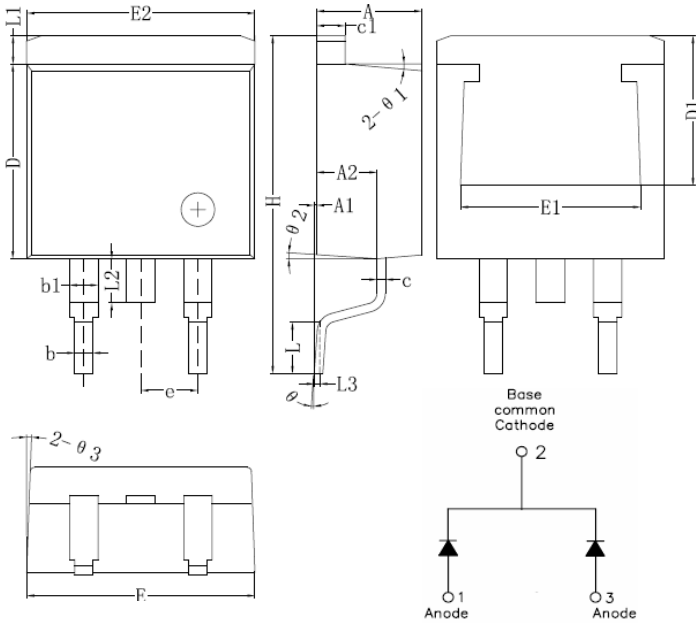
Case styles		
30CTQ...  TO-220AB	30CTQ...S  D²PAK	30CTQ...-1  TO-262

Mechanical Dimensions: In Inches / mm



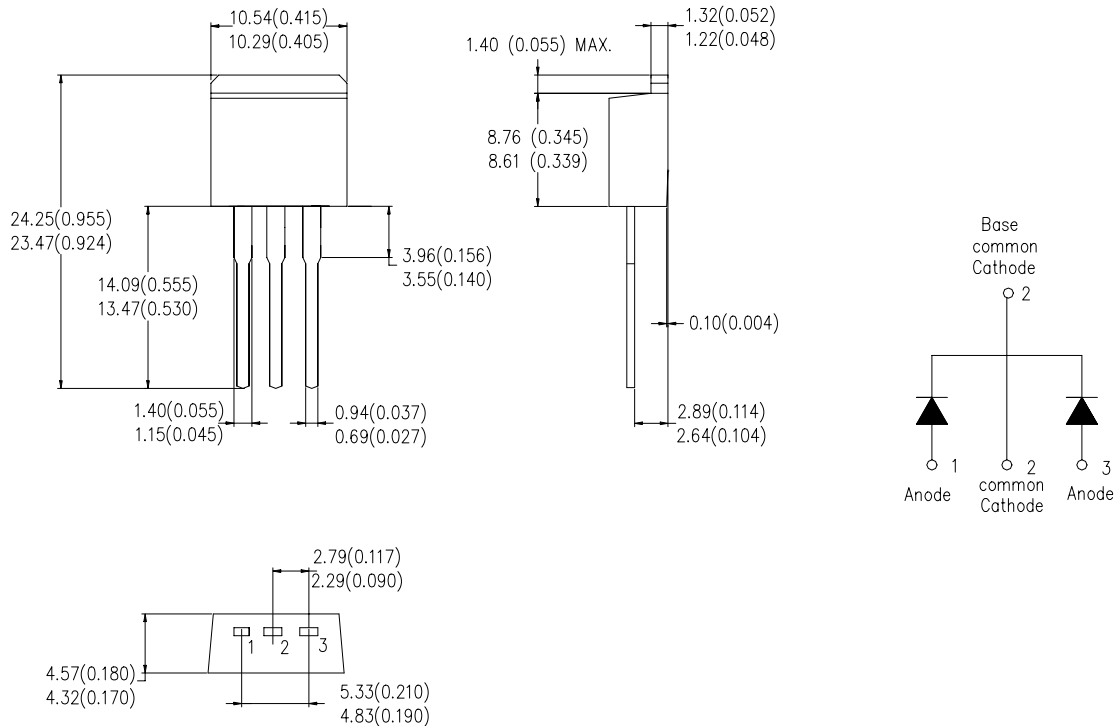
Symbol	Dimensions in millimeters		
	Min	Typical	Max
A	4.42	4.57	4.72
A1	1.17	1.27	1.37
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
D	14.94	15.24	15.54
D1	8.85	9.00	9.15
E	10.01	10.16	10.31
e		2.54	
e1		5.06	
H1	6.04	6.24	6.44
L	12.7	13.56	13.78
L1		3.5	
ΦP	3.74	3.84	4.04
Q	2.54	2.74	2.94
θ1		7°	
θ2		3°	
θ3		4°	

TO-220AB



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.55	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1		1.27	
c	0.36	0.38	0.61
c1	1.17	1.27	1.37
D	8.55	8.70	8.85
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.18
e		2.54	
H	14.6	15.1	15.6
L	2.00	2.30	2.70
L1	1.17	1.27	1.40
L2			2.20
L3		0.25BSC	
e	0	-	8°
e1		5°	
e2		4°	
e3		4°	

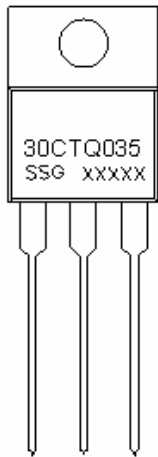
D²PAK



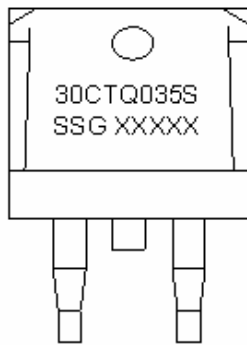
TO-262



Marking Diagram:



30CTQ035



30CTQ035S

Where XXXXX is YYWWL

30CTQ035 =Part Name
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
30CTQ...	TO-220AB (Pb-Free)	50pcs / tube
30CTQ...S	D ² PAK (Pb-Free)	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	35(30CTQ035) 40(30CTQ040) 45(30CTQ045)	V
Max. Average Forward	$I_{F(AV)}$	50% duty cycle @ $T_C = 127^\circ\text{C}$, rectangular wave form	30	A
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	318	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop (per leg) *	V _{F1}	@ 15A, Pulse, T _J = 25 °C	0.62	V
	V _{F2}	@ 15A, Pulse, T _J = 125 °C	0.56	V
Max. Reverse Current (per leg) *	I _{R1}	@V _R = rated V _R T _J = 25 °C	1.0	mA
	I _{R2}	@V _R = rated V _R T _J = 100°C	15	mA
Max. Junction Capacitance (per leg)	C _T	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	900	pF
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs

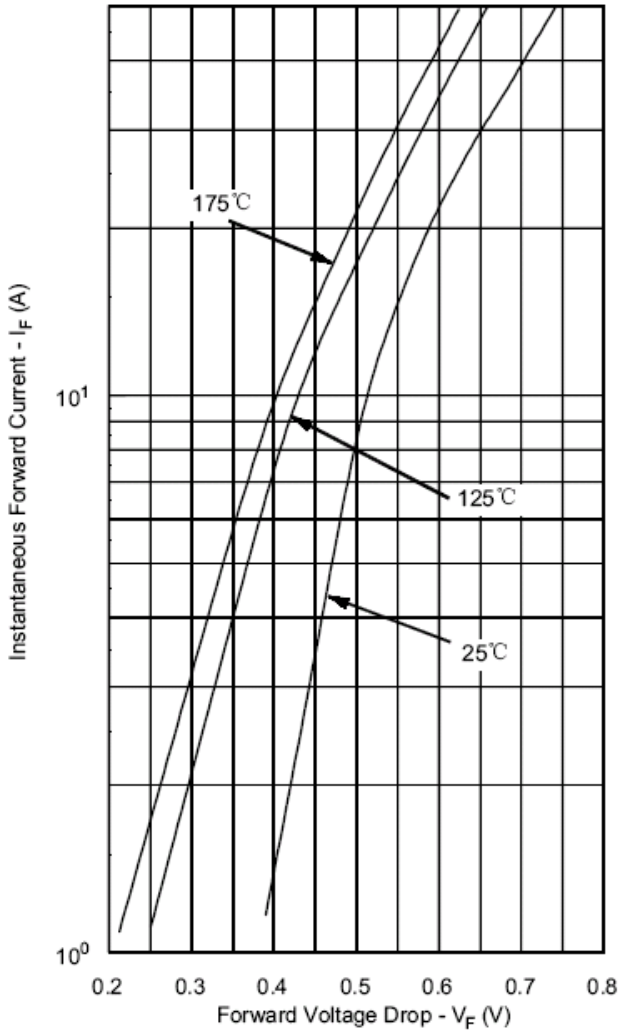
* Pulse Width < 300μs, Duty Cycle <2%

Thermal-Mechanical Specifications:

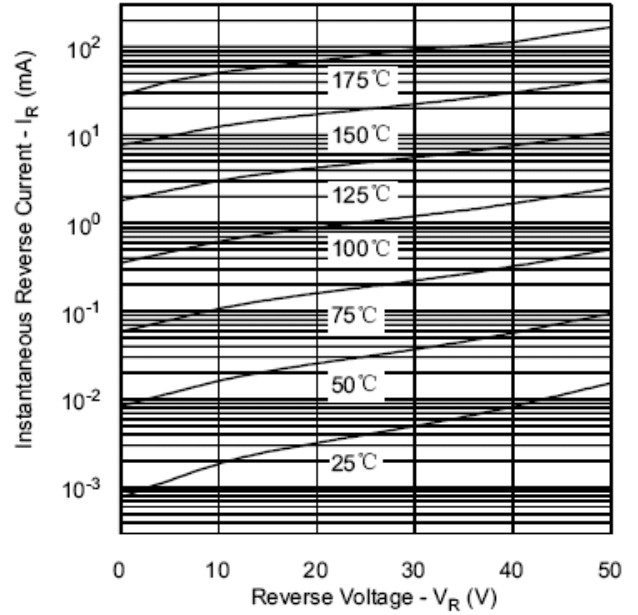
Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T _J	-	-55 to +175	°C
Max. Storage Temperature	T _{stg}	-	-55 to +175	°C
Maximum Thermal Resistance Junction to Case	R _{θJC}	DC operation	3.25	°C/W
Approximate Weight	wt	-	2/1.85	g
Case Style	TO-220AB D ² PAK TO-262(Suffix"-1" for TO-262;"S" for D ² PAK)			



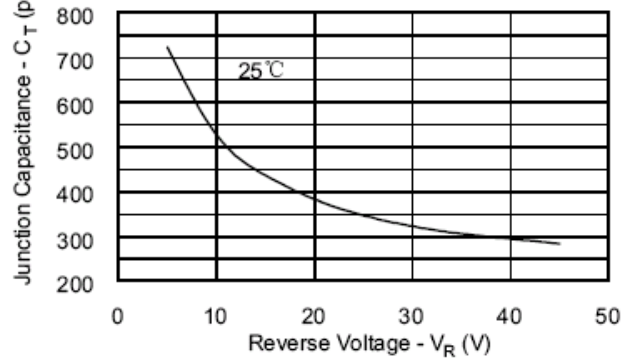
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance



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